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## U.S. Patent Documents

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## Foreign Patent Documents

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						Yes	No

## Other Documents (Including Author, Title, Date Pertinent Pages, Etc.)

		Japanese Office Action dated June 23, 2009
		Norio Onojima et al., "Lattice Relaxation Process of AlN Growth on Atomically Flat 6H-SiC Substrate in Molecular Beam Epitaxy", Journal of Crystal Growth (2002), pp. 1012-1016
		Steve Wright et al., "Reduction of Oxides on Silicon by Heating in a Gallium Molecular Beam at 800°C", Appl. Phys. Lett, Vol. 36, No. 3, 1 February 1980, pp. 210-211
EXAMINER		DATE CONSIDERED

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